

## SI2301CDS-T1-GE3-VB Datasheet

### P-Channel 20-V (D-S) MOSFET

#### MOSFET PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
- 20	0.060 at $V_{GS} = -10$ V	- 4.0	10 nC
	0.065 at $V_{GS} = -4.5$ V	- 3.5	
	0.080 at $V_{GS} = -2.5$ V	- 2.0	

#### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

#### APPLICATIONS

- Load Switch
- PA Switch
- DC/DC Converters



#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	- 20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current ( $T_J = 150$ °C)	$T_C = 25$ °C	- 4 <sup>e</sup>	A
	$T_C = 70$ °C	- 3.2	
	$T_A = 25$ °C	- 3.5 <sup>b, c</sup>	
	$T_A = 70$ °C	- 2.5 <sup>b, c</sup>	
Pulsed Drain Current	$I_{DM}$	- 10	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	- 2.1	
	$T_A = 25$ °C	- 1.0 <sup>b, c</sup>	
Maximum Power Dissipation	$T_C = 25$ °C	2.5	W
	$T_C = 70$ °C	1.6	
	$T_A = 25$ °C	1.25 <sup>b, c</sup>	
	$T_A = 70$ °C	0.8 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	$R_{thJA}$	75	100	°C/W
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	40	50	

Notes:

- Based on  $T_C = 25$  °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$  s.
- Maximum under steady state conditions is 166 °C/W.
- Package limited.

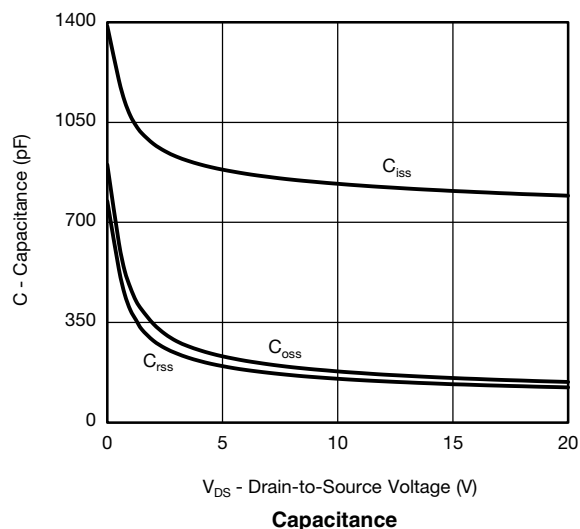
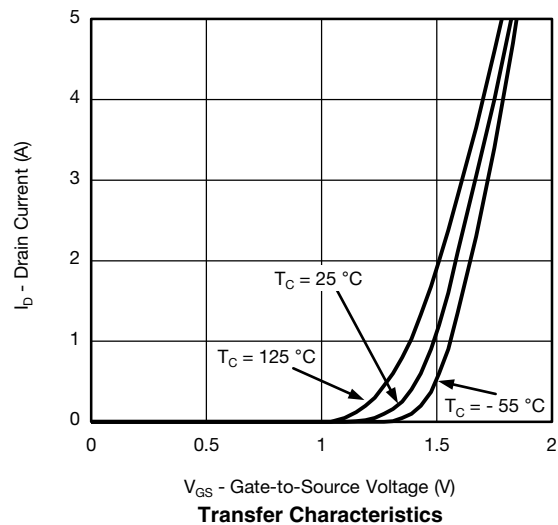
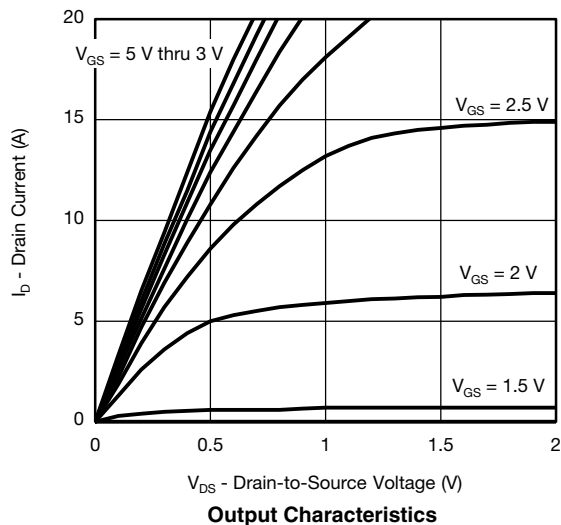
MOSFET SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>DS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 20			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = - 250 μA		- 13.4		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			2.9		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 0.5		- 1.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	μA
		V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ - 5 V, V <sub>GS</sub> = - 4.5 V	- 10			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3 A		0.060		Ω
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 2.5 A		0.065		
		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 2 A		0.080		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 3 A		15		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		835		pF
Output Capacitance	C <sub>oss</sub>			180		
Reverse Transfer Capacitance	C <sub>rss</sub>			155		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.1 A		10		nC
		V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 3.1 A		6.4		
Q <sub>gs</sub>			1.7			
Gate-Drain Charge	Q <sub>gd</sub>			3.4		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.9	4.4	8.8	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 10 V, R <sub>L</sub> = 2.4 Ω I <sub>D</sub> = - 3.1 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω		22	33	ns
Rise Time	t <sub>r</sub>			20	30	
Turn-Off Delay Time	t <sub>d(off)</sub>			28	42	
Fall Time	t <sub>f</sub>			9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 2.1	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 1 0	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 3.1 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 3.1 A, dl/dt = 100 A/μs, T <sub>J</sub> = 25 °C		23	35	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			12	20	nC
Reverse Recovery Fall Time	t <sub>a</sub>			15		ns
Reverse Recovery Rise Time	t <sub>b</sub>			8		

Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

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\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


**SOT-23 (TO-236): 3-LEAD**



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)



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